

18. (Not amended) A material according to claim 17, having a saturation moisture absorption of 1.0% by volume or less.

B2
19. (Amended) A material according to claim 17, having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher when a semiconductor has been bonded to a support member using said material.

20. (Amended) A material according to claim 18, having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher when a semiconductor has been bonded to a support member with said material.

21. (Not amended) A material according to claim 20, said material having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

22. (Not amended) A material according to claim 17, said material having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

B3
23. (Amended) A material according to claim 22, having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher when a semiconductor has been bonded to a support member with said material.

24. (Canceled)

25. (Canceled)

26. (Canceled)

27. (Canceled)

28. (Canceled)

29. (Canceled)

30. (Canceled)
31. (Canceled)
32. (Canceled)
33. (Canceled)
34. (Canceled)

B4

35. (Amended) A material according to claim 17, said component including a polyimide resin.

36. (Canceled)
37. (Canceled)
38. (Canceled)
39. (Canceled)

B5

40. (Amended) A material comprising an organic die-bonding film according to claim 17, further including an inorganic filler.

41. (Canceled)

42. (Amended) A method of bonding a semiconductor chip to a support member, the method comprising the steps of:

B4
providing a material comprising an organic die-bonding film having a water absorption of 1.5% by volume or less, and the material includes an epoxy resin wherein the epoxy resin is any one of glycidyl ether, glycidylamine, glycidyl ester and an alicyclic epoxy resin; and
bonding a semiconductor chip to a support member using the material.

43. (Not amended) A method of bonding according to claim 42, wherein said bonding is carried out at a temperature of 100-350°C for a time period of 0.1 second – 20 seconds with a pressure of 0.1 - 20gf/mm².

44. (Not amended) A method of bonding according to claim 43, wherein said bonding is carried out at a temperature of 150 - 250°C for a time period not longer than 2 seconds, with a pressure of 4 gf/mm² or less.

45. (Not amended) A method of bonding according to claim 44, wherein said bonding is carried out for a time period 1.5 seconds or less, with a pressure of 0.3 – 2 gf/mm².

46. (Canceled)

47. (Canceled)

48. (Canceled)

49. (Canceled)

50. (Amended) A semiconductor device comprising:

a semiconductor chip;

a support member; and

B7
a material comprising an organic die-bonding film having a water absorption of 1.5% by volume or less, and the material includes an epoxy resin wherein the epoxy resin is any one of glycidyl ether, glycidylamine, glycidyl ester and an alicyclic epoxy resin, wherein the material is provided between the semiconductor chip and the support member.

51. (Canceled)